



# Two Fast Approaches for 3D Thermal Simulation of Integrated Circuits

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Background

3D FVM for IC Thermal Simulation

Domain Decomposition Techniques

A Hybrid Random Walk Method

Conclusions

## Background

#### Motivation of IC thermal analysis

- The devices in an IC continuously increase
- Heat dissipation and thermal management become problems threatening circuit reliability and performance
- Chip-level thermal analysis (simulation): sign-off stage, also

for design-time circuit optimizations

- □ 3D IC is a trend: reduce delay, enable heterogeneous integration
- Severe heat dissipation problem
- Importance of accurate thermal simulation during design



Handle Silicon

Tier-1

Wafer-1

## Background

### Chip-level thermal simulation

- Should consider heat sink components
- Simulating the whole IC thermal model<sup>1</sup>
  - (w/ irregular geometry) brings computational challenges

#### Existing works

- **1.**Consider simplified rectangular domain
- □[Li, ICCAD'04]: Geometric multigrid iterative
- **[Zhan, TCAD'07]:** Green's function based

onal challenges



- cause > 10°C error ! 2.Consider realistic pyramid-geometry domain
- [Heriz, Thermal'07]: Convolution based, only for low-resolution
- [Qian, ICCAD'10-TODAES'12]: Fast Poisson solver (FPS)+PCG, with increased unknowns and geometry-dependent <u>convergence</u>

### **3D FVM for Thermal Simulation**

#### Problem formulation

3D steady-state heat equation

$$k \cdot \left(\frac{\partial^2 T(x, y, z)}{\partial x^2} + \frac{\partial^2 T(x, y, z)}{\partial y^2} + \frac{\partial^2 T(x, y, z)}{\partial z^2}\right) = -p(x, y, z)$$

Boundary conditions: Neumann (adiabatic) condition, convective condition  $k \frac{\partial T}{\partial \vec{n}} + h(T - T_{amb}) = 0$ 

Finite difference (volume) discretization



Thermal resistor!



## **3D FVM for Thermal Simulation**

#### Practical considerations

□Inhomogeneous material in IC region



To simplify, approximate the interconnect layer with a homogeneous layer  $k_{eff} = r_{metal} \cdot k_{cooper} + (1 - r_{metal}) \cdot k_{oxide}$ 

Power source resembles current source; solve equivalent circuit equation: AT = f Huge dimension!

heat sink

Two observations

⊇Subdomain geometry regulari<mark>ty <sup>| spreader</mark></mark></sup>

Concern only the die region

6

substrate

A general method for simulating complex domain

Nonoverlapping DDM from FVM-circuit viewpoint

- The solution of  $\Omega_2$  provides Dirichlet boundary boundary condition for  $\Omega_1$
- The heat flow at the bottom of  $\Omega_1$ provides Neumann condition for  $\Omega_2$

Different iteration schemes

- Top-to-bottom order
- Bottom-to-top order
- Middle-to-end order
- End-to-middle order

Check convergence w/ the interfacial quantities

Relaxed iterative scheme:

$$T_{V1}^{(i+1)} = T_{V1}^{(i)} + \omega (\tilde{T}_{V1}^{(i+1)} - T_{V1}^{(i)})$$

Nested two-subdomain order (more reliable but costly)



Nonconformal discretization

- Solve subdomains separately
- Much coarser discretization used for heat spreader/sink



8

- Linear interpolation converting quantities across interface; less affects the temperature in IC subdomain
- Exploit the regularity of subdomain
  - With conductivity homogenization, most subdomains are rectangular ones with simple configurations and conditions
  - FPS [Qian, ICCAD'10] with O(nlogn) time-complexity and O(n) space-complexity used for solving subdomains

#### Test cases

- Case 1: A 2D chip imitating the Power6 (175W in 1.6x2 die)
- Case 2: A 4-core 2D chip (176W in 1x1 die)
- Case 3: A 3D chip with Case 1+ 2 SRAM dies

#### Experiments

- Apply conformal discretization, and compare with Matlab "\" ICT-PCG, AMG-PCG (the fastest iterative PG solver), and FPS-PCG
- □With the result of Matlab "\", check accuracy
- Apply nonconformal discretization, to show efficiency improvement
- Use the simulator in heat sink component design



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Matrix	n	··/»	ICT-PCG		AMG-PCG			DDM		
		Time(s)	Iter.	Time(s)	Iter.	Time(s)	Mem.	Time(s)	Mem.	
M1-1	1.45e5	35.4	75	16.7	16	1.15	14MB	1.20	< 8MB	
M1-2	1.51e5	38.9	75	16.8	13	1.01	33MB	1.28	< 8MB	
M1-3	3.42e5	331.5	110	43.1	14	2.63	72MB	2.48	< 8MB	
M1-4	5.47e6				15	51.1	1.1GB	32.3	80MB	
M1-5	1.51e7				14	142.6	3.0GB	90.7	218MB	
M1-6	3.42e7							207.2	494MB	
M2-1	8.97e4	18.4	66	6.88	12	0.52	14MB	0.82	< 10MB	
M2-2	1.40e5	43.4	78	16.7	12	0.89	31MB	1.13	<10MB	
M3-3	3.59e5	359.3	103	204.9	12	2.68	78MB	2.21	<10MB	
M2-4	3.51e6				12	26.63	718MB	20.5	55MB	
M2-5	1.40e7				13	124.6	2.8GB	80.1	217MB	
M2-6	3.31e7							185.2	493MB	
M3-1	1.50e5	39.6	77	16.8	13	1.08	18MB	1.28	< 8MB	
M3-2	1.55e5	40.8	77	16.9	13	1.11	37MB	1.32	< 8MB	
M3-3	3.46e5	493.4	112	33.3	14	2.81	78MB	2.61	< 8MB	
M3-4	5.54e6				14	49.1	1.1GB	33.5	80MB	
M3-5	1.55e7				15	160.8	3.1GB	92.4	218MB	
M3-6	3.46e7							209.1	494MB	

- >10X memory savel
- Faster than iterative solvers for large case
- Converge in 8, 9 steps



 The temperature error in IC region is<sub>10</sub> less than 0.01 °C

#### Nonconformal discretization

Matrix	Co	nformal	grid	Non-conformal grid						
	n	Time(s)	T <sub>max</sub> (°C)	n	Time(s)	T <sub>max</sub> (°C)	Errmax(°C)	Speedur		
N	11-4	5.47e6	32.3	61.89	5.73e5	3.86	61.90	0.11	8.4	
Ν	11-5	1.51e7	90.7	61.97	1.65e6	8.98	61.95	0.03	10.1	
N	11-6	3.42e7	203.2	61.88	1.99e6	11.2	61.85	0.04	18	
Μ	1-10	5.41e7	310.1	61.85	3.22e6	18.5	61.84	0.02	17	

Apply to larger case

 < 0.05 °C Erro on hot spot

>10X memory save

### High-resolution simulation and design

- □ 1.05×10<sup>7</sup> unknown (50µm discretization-step) in IC region, needs 72s simulation time
- Study the temperature variations with the widths of heat spreader/sink changed
- 24-configuration simulation costs 7 mins.



Thermal simulation for hot-spots at device layer Entire temperature profile is often not required Random walk method for thermal analysis Equivalent to the P/G analysis problem, w/ thermal resistors P/G Random walk methods [Qian, TCAD'05][Miyakawa, GLSVLSI'11] □ [Wong, DATE'06]: used for  $V_x = \sum \frac{g_i}{\sum g_i} V_i - \frac{I_x}{\sum g_i}$ thermal via planning in 3D IC Drawbacks of existing works Not consider characteristics of IC thermal problem (boundary condition, geometry features) The computational speed is very slow

home

Generic random walk

### Main ideas

- Heat sink components (e.g. Pyramid-shape)
- Slow speed of RW (called GRW) is due to the long length of a walk path
- Another RW (FRW) is able to reduce the length of a walk path
- FRW encounters difficulty if there are the *source item* and Neumann, convective boundary condition



### GRW+FRW



#### Test cases

Case 1: A 4-core 2D chip (176W in 1x1 die)

Case 2: A 2D chip imitating the Power6 (175W in 1.6x2 die)

Experimental results

Hybrid0: GRW+FRW; Hybrid1: Neumann boundary treatment; Hybrid2: convective boundary treatment (1% 1-σ error)

Average runtime for calculating the temperature of a node (s)

Test	#node	GRW			Hybrid random walk					
case		time	#walk	#hop	hybrid0	hybrid1	hybrid2	#hop	Sp*	
1-1	5.24e5	49.8	5471	2.34e5	25.6	23.5	2.76	8.77e3	18	
1-2	4.19e6	199	5522	9.28e5	44.8	33.3	4.12	8.13e3	48	
1-3	6.55e7	949	6409	5.64e6	54.1	38.8	3.64	7.52e3	261	
2-1	5.33e5	35.5	3576	2.52e5	30.1	25.0	1.26	1.05e4	28	
2-2	4.26e6	143	3709	9.90e5	41.5	37.6	2.85	1.79e4	50	
2-3	6.66e7	762	3281	5.98e6	72.7	48.1	5.17	3.12e4	147	

#### Experimental results

- Memory overhead: ~81MB for transition-domain characterization
- The pre-characterization runs only once for same chip structure or chips manufactured by same materials
- Accuracy validated by Matlab "\"
- How the aspect ratio of the cuboid transition domain in FRW affects the efficiency of the proposed hybrid method ?
- Average Hybrid1's runtime for calculating a node's temperature (s)

Aspect ratio15810121520Time/node17043.341.941.340.941.842.5

Choosing cuboid transition domain (a.r.=10) brings 4.1X speedup

16

### Conclusions

Domain decomposition method

- Make the fast thermal solvers workable while appreciating the effect of heat sink components
- Can beat iterative equation solver for large case
- Nonconformal discretization grid reduces the computation with negligible loss of accuracy
- Hybrid random walk method
  - Combining GRW and FRW brings one or two orders of magnitude speedup, with some memory overhead
  - Suitable for the scenarios where only the temperature of some local hot-spots is needed

# Thanks!

18